

Innovating Test Technologies for production probe cards

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Assessing Pad Damage and Bond Integrity for Fine Pitch Probing

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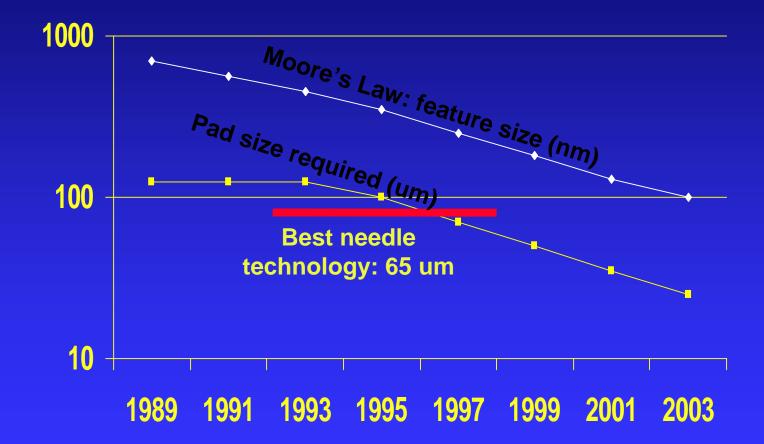
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- Challenges of die shrinks using finer geometry processing include wafer test and packaging
- Ball bonding used to be the gating technology to go to finer pitches and smaller pad sizes
- Ball bonder machines have solved their problems and have machines for production down to 50 micron pitches
- Probe technology now becomes the bottleneck to get to finer pitches and smaller pad size devices
- Requires a new technology to meet these challenges



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CHIP SHRINKS DRIVE THE CHANGES





Pad Pitch Roadmap*

80 70 60 Pad Pitch (microns) 50 Projected pad pitch SIA Roedmap 40 Theoretical pad pitch 30 **Projected physical** 20 limit of process/materials 10 **R&D** required 0 Solution under 2003 2006 2009 2012 1999 2001 1997 development Voor

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and the second second	1997	1999	2001	2003	2006	2009	2012
Fine line (µm)	0.25	0.18	0.15	0.13	0,1	0.07	0.05
% of reduction normalized		28%	17%	13%	23%	30%	29%
Projected pad pilch SIA	70	50	50	50	50	50	50
Theoretical pad pitch		50.4	42	36	28	19.6	14

*1998 SIA Roadmap



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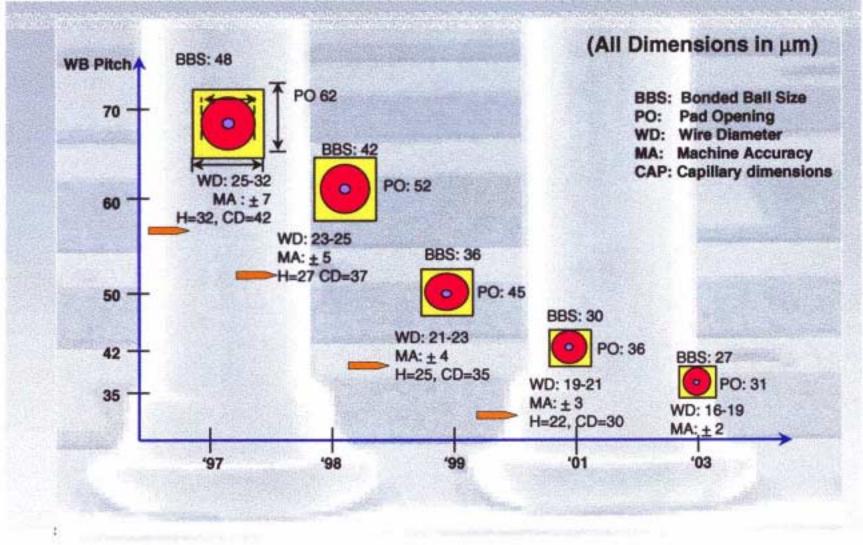
Ball Bonding Technology has arrived to meet these challenges

Ball Bonder specifications required for 50 Micron Pitch

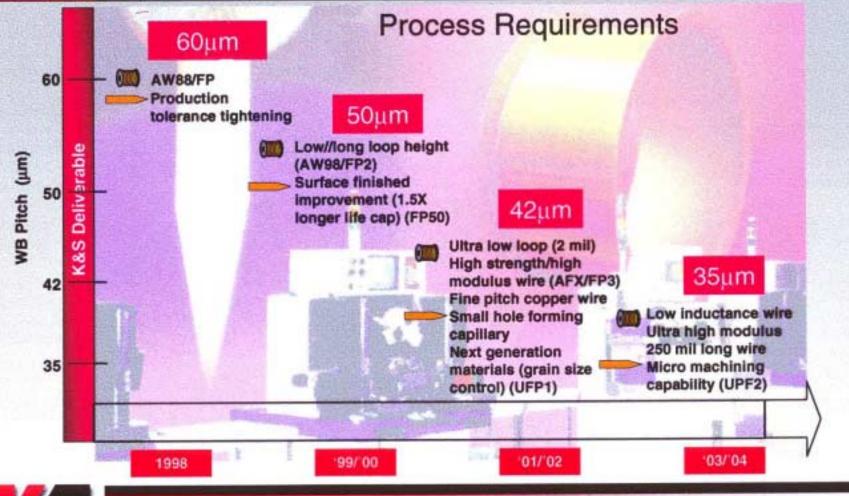
- Bonded Ball Size (BBS)
 - 36 microns for a 45 micron pad (50 micron pitch)
- Finer wire diameters (WD)
 - 21-23 microns
- Machine accuracy (MA)
 - $-\pm 4$ microns
- Capillary dimension (CD)
 - 35 microns



Process Requirement vs. Pad Pitch

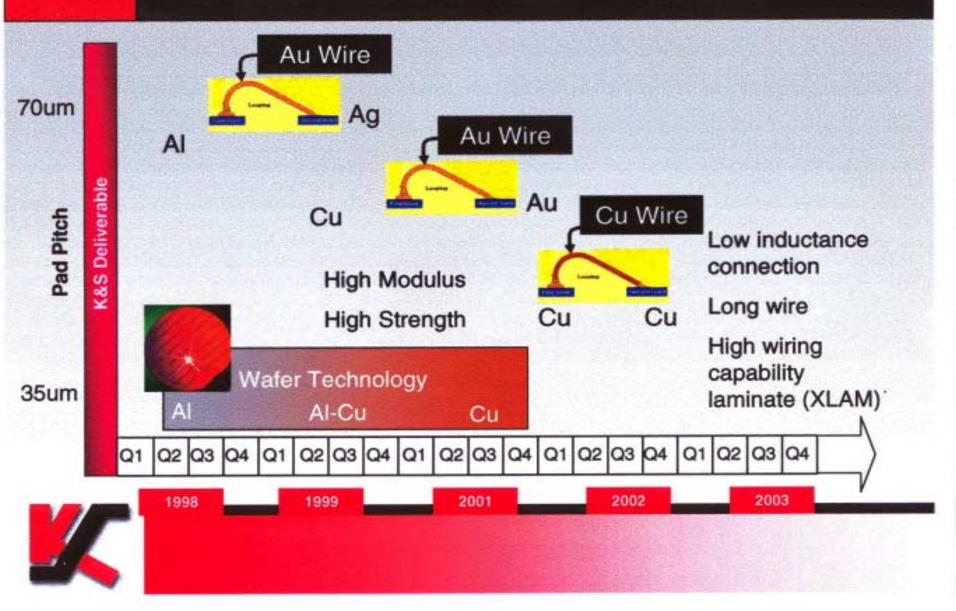


Ball Bonding Materials Roadmap





Evolution of Bond-to-Pad Technology





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Key Probe Parameters and Measurement Techniques

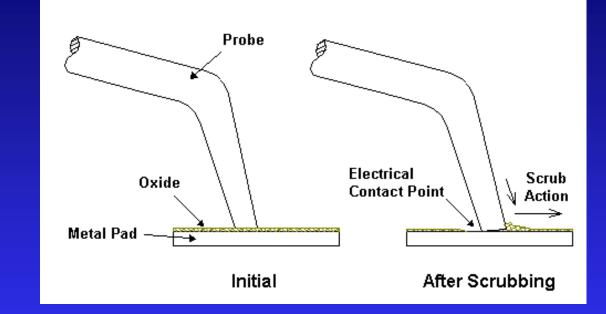
- Probe technology is key to being successful at wafer probing finer pitch devices
 - Placement accuracy (x-y dimensions)
 - Probe mark dimension and scrub length
 - Optical measurement techniques for dimension and placement accuracy
 - Pad damage from probe affects ball bond integrity and reliability
 - Stylus or optical profiler



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Epoxy Ring Probe needle

Cantilever beam scrubbing action



Typical tip diameter is 25 microns (1mil)
Typical scrub length is 15 microns
Typical x-y positional accuracy (± 5 micron)
Probe mark uncertainty (25 + 15 + 10) = 50 microns



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Standard Epoxy probe marks: note marks close to the edge of the passivation

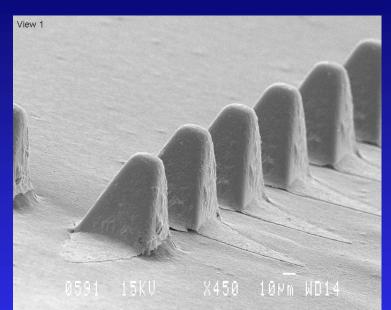
Enhanced needles tips to minimize probe mark, (80 micron pad size)





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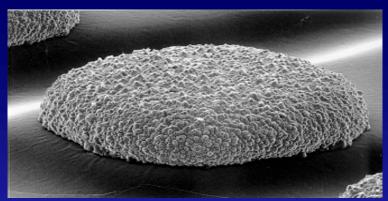
Different Pyramid Probe Tips



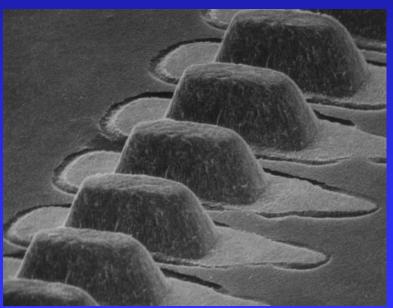
Probe tips for Al pads

- •15 micron diameter
- •60 micron tall

•80 micron pitch released production, have processed 40 micron pitch



Probe tips for Au pads and Solder bumps100 micron pitch, 60 micron contact area



Probe tips for gold bumps (LCD)50 micron pitch, 15 x 40 micron



Pyramid Probe tip Al Scrub Marks

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- Probe mark diameter- 15 microns
- 3 microns of scrub

Total probe mark dimension in y direction of 18 microns

X-Y placement
 accuracy of ±
 2 microns



Pyramid VS Cantilever

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SEM photo of needle tip and pyramid tip

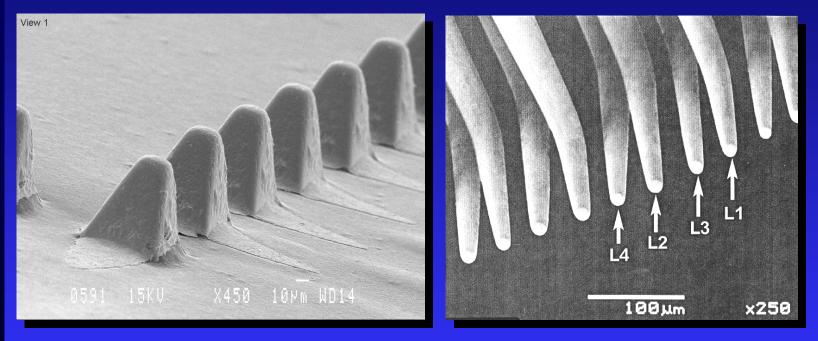


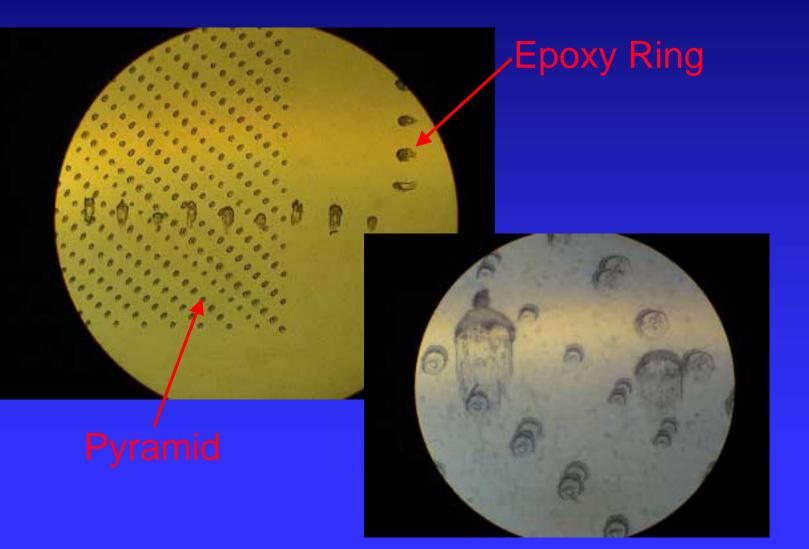
Photo-lithograph placed Pyramid Probe tips with 15 micron contact area at 60 micron pitch

Four tiers of needles mechanically placed to achieve 40 micron pitch



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Pyramid Probe Marks vs Needle





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- How much pad damage is to much damage? Deformation of Bond Pad
 - to

Penetration to Under Pad Layers

(Bond Pad over Active Circuit) (Low K Dielectrics)

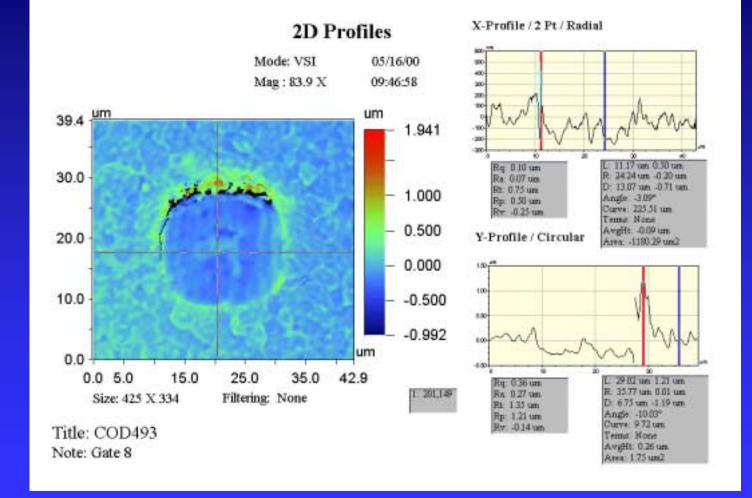
Long Term Reliability?

- Current Approach
 - Modeling
 - Internal Test
 - Customer Test
 - Pad Materials vs Pad Thickness
 - Cap Materials over Cu Pads
 - Cu Pads



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Profile of a Pyramid Probe mark taken with an Optical Profiler



Wyko profiler, range of .1 nm to 5 mm, resolution .1 nm



15 x Less Pad Damage

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Comparison of Pyramid vs Epoxy ring

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One Cantilever and two Pyramid Probe scrub marks from Sandia Labs test wafer

Pyramid damage85 cubic micronsEpoxy ring damage1447 cubic microns

Pyramid Probe marks Epoxy ring marks 15 x 20 microns

40 x 70 microns



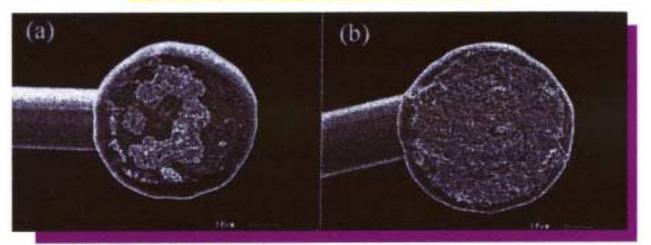
Elements of Fine Pitch — Ball Bonds

Shear/unit area effect on IP

What shear / area is required for reliable bonding?

A direct correlation can be seen between shear / area and growth of intermetallic phases (IP)

4.5 g/mil² \cong 35% IP coverage 5.5 g/mil² \cong 55% IP coverage 6.5 g/mil² \cong 75% IP coverage



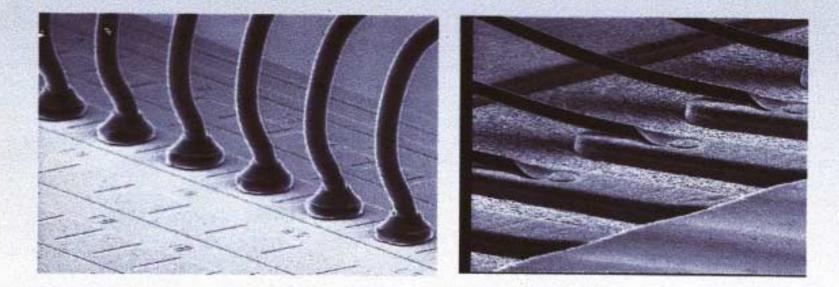
35% IP, 4.5 g/mil²

75% IP, 6.5 g/mil²



Cu Wire - Al Die

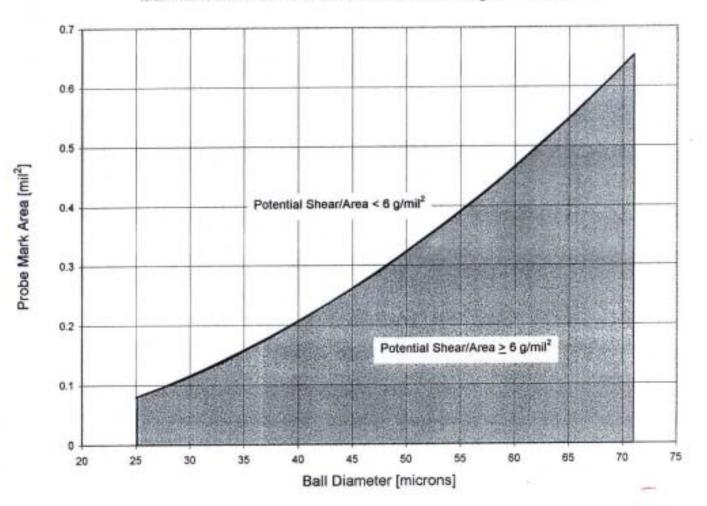
Program Status



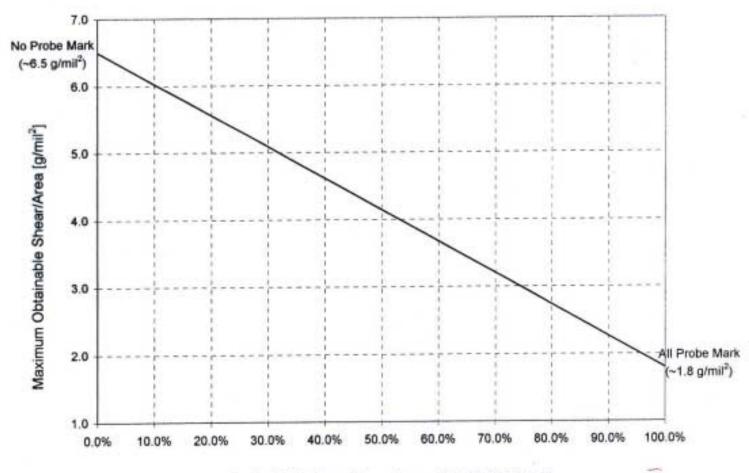
Ball Diameter: $\mu = 46.1 \ \mu m$, $\sigma = 0.43 \ \mu m$ Shear Strength: $\mu = 18.8g$, $\sigma = 1.1g$ (Shear/Area = 7.1g/mil²) Pull Strength: $\mu = 10.7$, $\sigma = 1.1g$



N. Murdeshwar

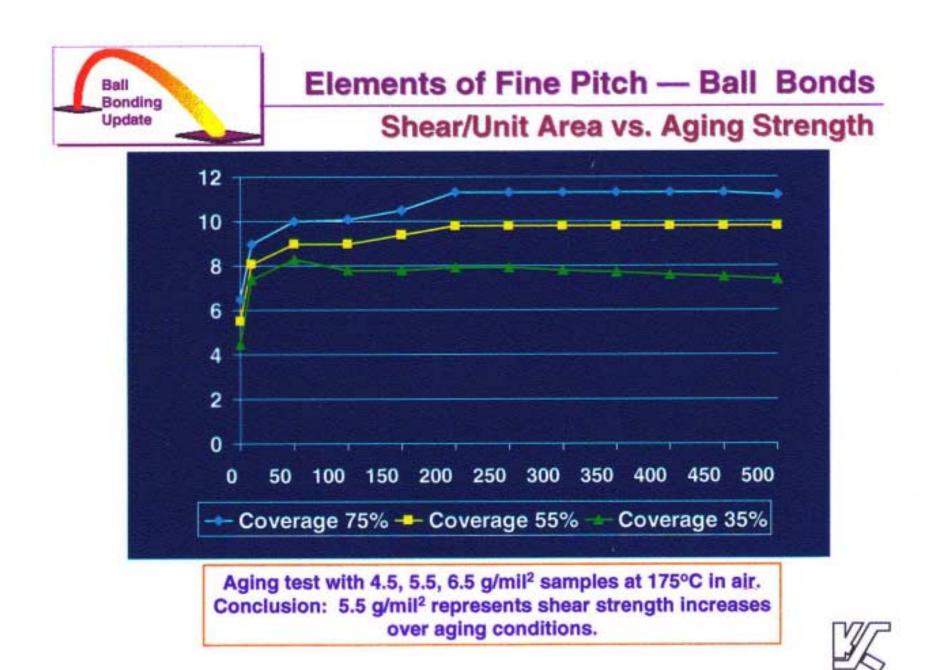


Maximum Allowable Probe Mark Area to Achieve 6 g/mil² Shear/Area



Maximum Obtainable Shear/Area for Given Probe Mark to Ball Area Ratio

Probe Mark Area (Percentage of Total Ball Area)





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Conclusions

- There are tools to measure and quantify pad damage due to probing
- There are tests to determine ball bond strength and reliability
- Ball bond technology can meet existing road maps
- There are probe technologies available to insure minimal pad damage, which maximizes bond strength and reliability
- Ongoing experiments with K&S, Cascade Microtech, and customers to further determine parameters required to meet pitch and pad size roadmaps